

Quarterly Reliability Monitoring Results

Quarters: Q1/2022 to Q4/2023

Based on structural similarity

Supplier Nexperia B.V.		User Part Number PMBT4403YS						
Nexperia DHAM Small Signal Bipolar Transistor								
SMD package								
Test Conditions	Duration	# Lots	# Quantity	# Rejects				
	TEST							
	Pre- and Post-Stress							
# E1	Electrical Test	Tamb = 25 °C	N/A	see below	all parts	see below		
		JESD22-A113						
		Bake Tamb = 125 °C	24 hours					
	PC	Soak Tamb = 85 °C, RH = 85%	168 hours					
# A1	Preconditioning	Reflow soldering	3 cycles	1674	70490	0		
		MIL-STD-750-1						
	HTRB	M1039 Method A						
	High Temperature Reverse Bias	Tj = Tjmax, Vr = 100% of max. datasheet				_		
# B1	DidS	reverse voltage	1000 hours	415	18680	0		
	тс	JECD22 A104						
# 14	Temperature Cycling	JESD22-A104 -65 °C to Timax, not to exceed 150°C	1000 eveles	242	15260	0		
# A4	remperature cycling	os e to rimax, not to exceed 150 e	1000 cycles	343	15360	U		
	UHAST	JESD22-A118						
# A3 or	Unbiased HAST	Tamb = 130 °C, RH = 85 %	96 hours	362	15920	0		
		JESD22-A102						
	AC	Tamb = 121 °C, RH = 100 %						
# A3 alt	Autoclave	Pressure = 205 kPa (29.7 psia)						
# 715 aic		,						
	H3TRB	JESD22-A101						
	High Humidity High	Tamb = 85 °C, RH = 85%, VR = 80 % of						
# A2 alt	Temperature Reverse Bias	rated reverse voltage ^[1]	1000 hours	343	15360	0		
	-	MIL-STD-750 Method 1037		-				
	IOL	ton = toff, devices powered to insure ΔT_j =						
# A5	Intermittent Operating Life		1000 hours	343	15360	0		
	RSH	JESD22-A111						
# C8	Resistance to Solder Heat	260 °C ± 5 °C	10 s	283	8490	0		
	SD							
# C10	Solderability	J-STD-002		214	6420	0		

^[1] The maximum applied voltage is limited by test chamber set up and does not exceed 115V.

Calculation of FIT and MTTF

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, Test #B1) Confidence level 60%, derated to 55 °C, activation energy 0.7 eV, test time 168 to 1000 hours

Wafer Fab	Technology	Quantity	Rejects	Failure Rate (FIT)	MTTF (hrs)
Nexperia	Small Signal Bipolar				
DHAM	Transistor	18680	0	0,23	4,40E+09

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